

What is claimed:

1. A polishing composition comprising an abrasive having an average primary particle size of 200 nm or less, an oxidizing agent, an acid having a pK<sub>1</sub> of 2 or less and/or a salt of an acid having as pK<sub>1</sub> of 2 or less, and water, wherein the acid having a pK<sub>1</sub> of 2 or less and/or the salt of an acid having a pK<sub>1</sub> of 2 or less is selected from the group consisting of sulfurous acid, persulfuric acid, phosphoric acid, phosphonic acid, phosphinic acid, pyrophosphoric acid, tripolyphosphoric acid and amide sulfuric acid, and wherein the acid value (Y) of the polishing composition is 20 mg KOH/g or less and 0.2 mg KOH/g or more.

2. The polishing composition according to claim 1, wherein the polishing composition has an acid value (Y) in the range 0.2 mg KOH/g through 5 mg KOH/g.

3. The polishing composition of claim 1 or 2, wherein the acid value (Y) of the polishing composition satisfies the formula (1):

$$Y(\text{mg KOH/g}) \leq 5.7 \times 10^{-17} \times X(/g) + 19.45 \quad (1)$$

wherein X is a concentration of the abrasive in the polishing composition on a numerical basis.

4. A process for reducing the amount of fine scratches imparted to a substrate during a polishing operation, comprising polishing a substrate to be polished with the polishing composition of any one of claims 1 to 2.

5. A process for reducing the amount of fine scratches imparted to a substrate during a polishing operation, comprising polishing a substrate to be polished with the polishing composition of claim 3.

6. A method for manufacturing a substrate, comprising the step of polishing a substrate to be polished during a manufacturing process with the polishing composition of any one of claims 1 to 2.

7. A method for manufacturing a substrate, comprising the step of polishing a substrate to be polished during a manufacturing process with the polishing composition of claim 3.